

LISTING OF THE CLAIMS:

Claims 1-29 (Cancelled)

Claim 30. (Currently amended) A field effect transistor comprising:

a substrate of a single crystal semiconducting material,

two spaced apart metal semiconductor compound regions forming a source and drain and defining a channel there between,

a first dielectric layer on said two spaced apart metal semiconductor compound regions ~~source and drain adjacent said channel~~,

a gate dielectric layer of locally reacted metal of said metal used in said metal-semiconductor compound regions on said channel located beneath said two spaced apart metal semiconductor compound regions, and

a conductive layer on said ~~gate dielectric layer to form a gate~~ first dielectric layer and in contact with said gate dielectric layer to form a gate, wherein said first dielectric layer extends under sidewalls of said conductive layer.

Claims 31-32 (Cancelled)

Claim 33. (Original) The field effect transistor of claim 30 wherein said gate dielectric layer includes TiO_2 .

Claims 34-64 (Cancelled)

Claim 65. (previously presented) The field effect transistor of claim 30 wherein said two spaced apart metal semiconductor compound regions further include an additional layer of conductive material between said metal and said first dielectric layer, said additional layer of conductive material having sidewalls, said sidewalls having insulating material disposed thereon.

Claim 66. (previously presented) The field effect transistor of claim 65 wherein said additional layer of conductive material includes an oxidizable material.

Claim 67. (previously presented) The field effect transistor of claim 65 wherein said additional layer of conductive material is selected from the group consisting of Al, Co, Er, Ni, Pd, Pt, Rh, Ta, Ti and W.

Claim 68. (previously presented) The field effect transistor of claim 65 wherein said metal of said metal semiconductor compound regions is selected from the group consisting of Al, Co, Er, Ni, Pd, Pt, Rh, Ta, Ti, and W.

Claim 69. (previously presented) The field effect transistor of claim 65 wherein said two spacer apart metal semiconductor compound regions include Ta and said additional layer of conductive material includes Al.

Claim 70. (previously presented) The field effect transistor of claim 65 wherein said insulating material disposed on said sidewalls of said additional layer of conductive material also covers sidewalls of said first dielectric layer.

Claim 71. (previously presented) The field effect transistor of claim 65 wherein said insulating material disposed on said sidewalls of said additional layer of conductive material includes an oxide of said additional conductive material.

Claim 72. (Newly added) A field effect transistor comprising:
a metal layer atop a substrate, said metal layer comprising metal semiconductor regions adjacent to a locally reacted region, wherein said metal semiconductor regions atop said substrate form source/drain regions;

a dielectric layer atop each of said metal semiconductor regions; and

a conductive layer on said locally reacted region, wherein said conductive layer on said locally reacted region form a gate.